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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, HDMI-CEC, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16К х 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f072cbt6

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F072x8/xB microcontrollers.

This document should be read in conjunction with the STM32F0xxxx reference manual (RM0091). The reference manual is available from the STMicroelectronics website *www.st.com*.

For information on the ARM[®] Cortex[®]-M0 core, please refer to the Cortex[®]-M0 Technical Reference Manual, available from the www.arm.com website.





Analog I/O group	Number of capacitive sensing channels							
	STM32F072Vx	STM32F072Rx	STM32F072Cx					
G1	3	3	3					
G2	3	3	3					
G3	3	3	2					
G4	3	3	3					
G5	3	3	3					
G6	3	3	3					
G7	3	0	0					
G8	3	0	0					
Number of capacitive sensing channels	24	18	17					

Table 6. Number of capacitive sensing channels available on STM32F072x8/xB devices

3.14 Timers and watchdogs

The STM32F072x8/xB devices include up to six general-purpose timers, two basic timers and an advanced control timer.

Table 7 compares the features of the different timers.

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	3
	TIM2	32-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
General purpose	TIM3	16-bit	Up, down, up/down	integer from 1 to 65536	Yes	4	-
	TIM14	16-bit	Up	integer from 1 to 65536	No	1	-
	TIM15	16-bit	Up	integer from 1 to 65536	Yes	2	1
	TIM16 TIM17	16-bit	Up	integer from 1 to 65536	Yes	1	1
Basic	TIM6 TIM7	16-bit	Up	integer from 1 to 65536	Yes	-	-

Table 7. Timer feature comparison



Pinouts and pin descriptions



Figure 9. WLCSP49 package pinout



1. The above figure shows the package in top view, changing from bottom view in the previous document versions.



Pin name	AF0	AF1
PC0	EVENTOUT	-
PC1	EVENTOUT	-
PC2	EVENTOUT	SPI2_MISO, I2S2_MCK
PC3	EVENTOUT	SPI2_MOSI, I2S2_SD
PC4	EVENTOUT	USART3_TX
PC5	TSC_G3_IO1	USART3_RX
PC6	TIM3_CH1	-
PC7	TIM3_CH2	-
PC8	TIM3_CH3	-
PC9	TIM3_CH4	-
PC10	USART4_TX	USART3_TX
PC11	USART4_RX	USART3_RX
PC12	USART4_CK	USART3_CK
PC13	-	-
PC14	-	-
PC15	-	-

Table 16. Alternate functions selected through GPIOC_AFR registers for port C

Table 17. Alternate functions selected through GPIOD_AFR registers for port D

Pin name	AF0	AF1
PD0	CAN_RX	SPI2_NSS, I2S2_WS
PD1	CAN_TX	SPI2_SCK, I2S2_CK
PD2	TIM3_ETR	USART3_RTS
PD3	USART2_CTS	SPI2_MISO, I2S2_MCK
PD4	USART2_RTS	SPI2_MOSI, I2S2_SD
PD5	USART2_TX	-
PD6	USART2_RX	-
PD7	USART2_CK	-
PD8	USART3_TX	-
PD9	USART3_RX	-
PD10	USART3_CK	-
PD11	USART3_CTS	-
PD12	USART3_RTS	TSC_G8_IO1
PD13	-	TSC_G8_IO2
PD14	-	TSC_G8_IO3
PD15	CRS_SYNC	TSC_G8_IO4



5 Memory mapping

To the difference of STM32F072xB memory map in *Figure 10*, the two bottom code memory spaces of STM32F072x8 end at 0x0000 FFFF and 0x0800 FFFF, respectively.



Figure 10. STM32F072xB memory map



Bus	Boundary address	Size	Peripheral
	0x4000 7C00 - 0x4000 7FFF	1 KB	Reserved
	0x4000 7800 - 0x4000 7BFF	1 KB	CEC
	0x4000 7400 - 0x4000 77FF	1 KB	DAC
	0x4000 7000 - 0x4000 73FF	1 KB	PWR
	0x4000 6C00 - 0x4000 6FFF	1 KB	CRS
	0x4000 6800 - 0x4000 6BFF	1 KB	Reserved
	0x4000 6400 - 0x4000 67FF	1 KB	BxCAN
	0x4000 6000 - 0x4000 63FF	1 KB	USB/CAN RAM
	0x4000 5C00 - 0x4000 5FFF	1 KB	USB
	0x4000 5800 - 0x4000 5BFF	1 KB	I2C2
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1
	0x4000 5000 - 0x4000 53FF	1 KB	Reserved
	0x4000 4C00 - 0x4000 4FFF	1 KB	USART4
	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 3C00 - 0x4000 43FF	2 KB	Reserved
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
APB	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 2400 - 0x4000 27FF	1 KB	Reserved
	0x4000 2000 - 0x4000 23FF	1 KB	TIM14
	0x4000 1800 - 0x4000 1FFF	2 KB	Reserved
	0x4000 1400 - 0x4000 17FF	1 KB	TIM7
	0x4000 1000 - 0x4000 13FF	1 KB	TIM6
	0x4000 0800 - 0x4000 0FFF	2 KB	Reserved
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2

Table 20. STM32F072x8/xB peripheral register boundary addresses (continued)



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25$ °C and $T_A = T_A max$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25$ °C, $V_{DD} = V_{DDA} = 3.3$ V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 11*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 12*.





Sym- Para- bol meter		Conditions		Typ @V _{DD} (V _{DD} = V _{DDA})					Max ⁽¹⁾					
				2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 °C	Unit	
	Supply current in	Reg mod osc	gulator in run de, all illators OFF	15.4	15.5	15.6	15.7	15.8	15.9	23 ⁽²⁾	49	68 ⁽²⁾		
I _{DD}	Stop mode	Reg pow osc	Regulator in low- power mode, all oscillators OFF		3.3	3.4	3.5	3.6	3.7	8 ⁽²⁾	33	51 ⁽²⁾		
	Supply current in	LSI ON	ON and IWDG	0.8	1.0	1.1	1.2	1.3	1.4	-	-	-		
	Standby mode	LSI OFI	OFF and IWDG =	0.6	0.7	0.9	0.9	1.0	1.1	2.1 ⁽²⁾	2.6	3.1 ⁽²⁾		
	Supply current in Stop mode	Supply	z	Regulator in run mode, all oscillators OFF	2.1	2.2	2.3	2.5	2.6	2.8	3.5 ⁽²⁾	3.6	4.6 ⁽²⁾	
		_A monitoring O	Regulator in low-power mode, all oscillators OFF	2.1	2.2	2.3	2.5	2.6	2.8	3.5 ⁽²⁾	3.6	4.6 ⁽²⁾	μA	
	Supply 2 current in	V _{DC}	LSI ON and IWDG ON	2.5	2.7	2.8	3.0	3.2	3.5	-	-	-		
	Standby mode		LSI OFF and IWDG OFF	1.9	2.1	2.2	2.3	2.5	2.6	3.5 ⁽²⁾	3.6	4.6 ⁽²⁾		
IDDA	Supply current in Stop mode	Supply	H.	Regulator in run mode, all oscillators OFF	1.3	1.3	1.4	1.4	1.5	1.5	-	-	-	
		A monitoring Ol	Regulator in low-power mode, all oscillators OFF	1.3	1.3	1.4	1.4	1.5	1.5	-	-	-		
	Supply current in	V _{DD}	LSI ON and IWDG ON	1.7	1.8	1.9	2.0	2.1	2.2	-	-	-		
	Standby mode		LSI OFF and IWDG OFF	1.2	1.2	1.2	1.3	1.3	1.4	-	-	-		

Table 31. Typical and maximum consumption in Stop and Standby modes

1. Data based on characterization results, not tested in production unless otherwise specified.

2. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).



STM32F072x8 STM32F072xB

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Тур	Unit
			4 MHz	0.07	
			8 MHz	0.15	
		$C = C_{INT}$	16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
			4 MHz	0.18	
		V _{DDIOx} = 3.3 V	8 MHz	0.37	
		C _{EXT} = 0 pF	16 MHz	0.76	
		$C = C_{INT} + C_{EXT} + C_{S}$	24 MHz	1.39	
			48 MHz	2.188	
			4 MHz	0.32	
	I/O current consumption	$V_{DDIOx} = 3.3 V$ $C_{EXT} = 10 pF$ $C = C_{INT} + C_{EXT} + C_S$	8 MHz	0.64	mA
			16 MHz	1.25	
			24 MHz	2.23	
low			48 MHz	4.442	
.200		$V_{DDIOx} = 3.3 V$ $C_{EXT} = 22 pF$ $C = C_{INT} + C_{EXT} + C_S$	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
			4 MHz	0.64	
		$V_{\text{DDIOX}} = 3.3 \text{ V}$		8 MHz	1.25
		$C = C_{INT} + C_{EXT} + C_S$	16 MHz	3.24	
			24 MHz	5.02	
		V _{DDIOx} = 3.3 V	4 MHz	0.81	
		$C_{EXT} = 47 \text{ pF}$	8 MHz	1.7	
		$C = C_{INT} + C_{EXT} + C_{S}$ $C = C_{int}$	16 MHz	3.67	1
		V _{DDIOx} = 2.4 V	4 MHz	0.66	
		$C_{EXT} = 47 \text{ pF}$	8 MHz	1.43	
		$C = C_{INT} + C_{EXT} + C_{S}$	16 MHz	2.45	
		$C = C_{int}$	24 MHz	4.97	

Table 34. Switching output I/O current consumption

1. C_S = 7 pF (estimated value).



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 39*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Тур	Max ⁽²⁾	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
		During startup ⁽³⁾	-	-	8.5	
		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.4	-	
	HSE current consumption	V _{DD} = 3.3 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.5	-	
I _{DD}		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	mA
		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
9 _m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

Table 3	39. HSE	oscillator	characteristics

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by design, not tested in production.

3. This consumption level occurs during the first 2/3 of the $t_{\mbox{SU(HSE)}}$ startup time

4. t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



High-speed internal (HSI) RC oscillator

Parameter	Conditions	Min	Тур	Мах	Unit				
Frequency	-	-	8	-	MHz				
HSI user trimming step	-	-	-	1 ⁽²⁾	%				
Duty cycle	-	45 ⁽²⁾	-	55 ⁽²⁾	%				
	T _A = -40 to 105°C	-2.8 ⁽³⁾	-	3.8 ⁽³⁾					
	T _A = -10 to 85°C	-1.9 ⁽³⁾	-	2.3 ⁽³⁾	%				
Accuracy of the HSI oscillator	T _A = 0 to 85°C	-1.9 ⁽³⁾	-	2 ⁽³⁾					
	$T_A = 0$ to $70^{\circ}C$	-1.3 ⁽³⁾	-	2 ⁽³⁾					
	$T_A = 0$ to 55°C	-1 ⁽³⁾	-	2 ⁽³⁾					
	$T_{A} = 25^{\circ}C^{(4)}$	-1	-	1					
HSI oscillator startup time	-	1 ⁽²⁾	-	2 ⁽²⁾	μs				
HSI oscillator power consumption	-	-	80	100 ⁽²⁾	μA				
	Parameter Frequency HSI user trimming step Duty cycle Accuracy of the HSI oscillator HSI oscillator startup time HSI oscillator power consumption	ParameterConditionsFrequency-HSI user trimming step-Duty cycle-Accuracy of the HSI oscillator $T_A = -40 \text{ to } 105^{\circ}C$ $T_A = -10 \text{ to } 85^{\circ}C$ $T_A = 0 \text{ to } 70^{\circ}C$ $T_A = 0 \text{ to } 55^{\circ}C$ $T_A = 0 \text{ to } 55^{\circ}C$ $T_A = 25^{\circ}C^{(4)}$ HSI oscillator power consumption-	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min \\ \hline Frequency & - & - \\ \hline HSI user trimming step & - & - \\ \hline Duty cycle & - & 45^{(2)} \\ \hline T_A = -40 \ to \ 105^\circ C & -2.8^{(3)} \\ \hline T_A = -10 \ to \ 85^\circ C & -1.9^{(3)} \\ \hline T_A = 0 \ to \ 85^\circ C & -1.9^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1.3^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1^{(3)} \\ \hline T_A = 25^\circ C^{(4)} & -1 \\ \hline HSI \ oscillator \ power \\ consumption & - & 1^{(2)} \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c } \hline Parameter & Conditions & Min & Typ \\ \hline Frequency & - & - & 8 \\ \hline HSI user trimming step & - & - & - \\ \hline Duty cycle & - & 45^{(2)} & - \\ \hline Duty cycle & - & 45^{(2)} & - \\ \hline T_A = -40 to 105^\circ C & -2.8^{(3)} & - \\ \hline T_A = -10 to 85^\circ C & -1.9^{(3)} & - \\ \hline T_A = 0 to 85^\circ C & -1.9^{(3)} & - \\ \hline T_A = 0 to 70^\circ C & -1.3^{(3)} & - \\ \hline T_A = 0 to 55^\circ C & -1^{(3)} & - \\ \hline T_A = 0 to 55^\circ C & -1^{(3)} & - \\ \hline T_A = 25^\circ C^{(4)} & -1 & - \\ \hline HSI oscillator power & - & 1^{(2)} & - \\ \hline HSI oscillator power & - & - & 80 \\ \hline \end{tabular}$	$\begin{tabular}{ c c c c c } \hline Parameter & Conditions & Min & Typ & Max \\ \hline Frequency & - & - & 8 & - \\ \hline HSI user trimming step & - & - & 1(^2) \\ \hline Duty cycle & - & 45^{(2)} & - & 55^{(2)} \\ \hline T_A = -40 \ to \ 105^\circ C & -2.8^{(3)} & - & 3.8^{(3)} \\ \hline T_A = -10 \ to \ 85^\circ C & -1.9^{(3)} & - & 2.3^{(3)} \\ \hline T_A = 0 \ to \ 85^\circ C & -1.9^{(3)} & - & 2^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1.3^{(3)} & - & 2^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1^{(3)} & - & 2^{(3)} \\ \hline T_A = 0 \ to \ 55^\circ C & -1^{(3)} & - & 1 \\ \hline HSI \ oscillator \ startup \ time & - & 1^{(2)} & - & 1 \\ \hline HSI \ oscillator \ power \ consumption & - & 80 & 100^{(2)} \\ \hline \end{tabular}$				

Table 41. HSI oscillator characteristics⁽¹⁾

1. V_{DDA} = 3.3 V, T_A = -40 to 105°C unless otherwise specified.

2. Guaranteed by design, not tested in production.

3. Data based on characterization results, not tested in production.

4. Factory calibrated, parts not soldered.



Figure 19. HSI oscillator accuracy characterization results for soldered parts



Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored	Max vs. [f _{HSE} /f _{HCLK}]	Unit	
Gymbol		Conditions	frequency band	8/48 MHz		
S _{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	-2		
			30 to 130 MHz	27	dBµV	
			130 MHz to 1 GHz	17		
			EMI Level	4	-	

Table 49. EMI characteristics

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.



6.3.17 DAC electrical specifications

Symbol	Parameter	Min	Тур	Max	Unit	Comments
V _{DDA}	Analog supply voltage for DAC ON	2.4	-	3.6	V	-
D (1)	Resistive load with buffer	5	-	-	kΩ	Load connected to V _{SSA}
►LOAD` ′	ON	25	-	-	kΩ	Load connected to V _{DDA}
R _O ⁽¹⁾	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V _{SS} to have a 1% accuracy is 1.5 M Ω
C _{LOAD} ⁽¹⁾	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min ⁽¹⁾	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input
DAC_OUT max ⁽¹⁾	Higher DAC_OUT voltage with buffer ON	-	-	V _{DDA} – 0.2	V	$V_{DDA} = 3.6 V \text{ and } (0x155) \text{ and}$ (0xEAB) at $V_{DDA} = 2.4 V$
DAC_OUT min ⁽¹⁾	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output
DAC_OUT max ⁽¹⁾	Higher DAC_OUT voltage with buffer OFF	I	-	V _{DDA} – 1LSB	V	excursion of the DAC.
I (1)	DAC DC current	-	-	600	μA	With no load, middle code (0x800) on the input
'DDA'	mode ⁽²⁾	I	-	700	μA	With no load, worst code (0xF1C) on the input
DNL ⁽³⁾	Differential non linearity Difference between two	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
Ditte	consecutive code-1LSB)	-	-	±2	LSB	Given for the DAC in 12-bit configuration
	Integral non linearity (difference between	-	-	±1	LSB	Given for the DAC in 10-bit configuration
INL ⁽³⁾	and the value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±4	LSB	Given for the DAC in 12-bit configuration
	Offset error	-	-	±10	mV	-
Offset ⁽³⁾	(difference between measured value at Code	-	-	±3	LSB	Given for the DAC in 10-bit at V _{DDA} = 3.6 V
	(0x800) and the ideal value = V _{DDA} /2)	-	-	±12	LSB	Given for the DAC in 12-bit at $V_{DDA} = 3.6 V$

Table	60.	DAC	characteristics
Table	00.	DAO	character istics



6.3.18 Comparator characteristics

Symbol	Parameter	Conditio	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit	
V _{DDA}	Analog supply voltage	-	V _{DD}	-	3.6	V	
V _{IN}	Comparator input voltage range	-	0	-	V _{DDA}	-	
V _{SC}	V _{REFINT} scaler offset voltage	-	-	±5	±10	mV	
ts sc	V _{REFINT} scaler startup	First V _{REFINT} scaler activ	vation after device	-	-	1000 (2)	ms
0_00	time from power down	Next activations		-	-	0.2	
t _{START}	Comparator startup time	Startup time to reach pro specification	-	-	60	μs	
		Ultra-low power mode			2	4.5	μs
	Propagation delay for 200 mV step with 100 mV overdrive	Low power mode			0.7	1.5	
		Medium power mode	-	0.3	0.6		
		Lligh aroud mode	V _{DDA} ≥2.7 V	-	50	100	20
t_		nigh speed mode	V _{DDA} < 2.7 V	-	100	240	115
۲D	Propagation delay for full range step with 100 mV overdrive	Ultra-low power mode	-	2	7	μs	
		Low power mode	-	0.7	2.1		
		Medium power mode	-	0.3	1.2		
		High speed mode	V _{DDA} ≥ 2.7 V	-	90	180	ne
		nigh speed mode	V _{DDA} < 2.7 V	-	110	300	115
V _{offset}	Comparator offset error	-	-	±4	±10	mV	
dV _{offset} /dT	Offset error temperature coefficient	-	-	18	-	µV/°C	
		Ultra-low power mode	-	1.2	1.5		
	COMP current consumption	Low power mode			3	5	ıΔ
IDD(COMP)		Medium power mode		-	10	15	μΛ
		High speed mode		-	75	100	

Table 61. Comparator characteristics



Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.



 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

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Symbol	millimeters			inches ⁽¹⁾			
	Min	Тур	Мах	Min	Тур	Мах	
А	-	-	1.600	-	-	0.0630	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571	
b	0.170	0.220	0.270	0.0067	0.0087	0.0106	
с	0.090	-	0.200	0.0035	-	0.0079	
D	8.800	9.000	9.200	0.3465	0.3543	0.3622	
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
D3	-	5.500	-	-	0.2165	-	
E	8.800	9.000	9.200	0.3465	0.3543	0.3622	
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
E3	-	5.500	-	-	0.2165	-	
е	-	0.500	-	-	0.0197	-	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
k	0°	3.5°	7°	0°	3.5°	7°	
CCC	-	-	0.080	-	-	0.0031	

Table 78. LQFP48 package mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

1. Dimensions are expressed in millimeters.

